



100V NPN MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > 100V
- BV_{ECO} > 6V
- I_C = 2.5A Continuous Collector Current
- I_{CM} = 3.5A Peak Collector Current
- V_{CE(SAT)} < 100mV @ 1A
- $R_{CE(SAT)} = 80m\Omega$ for a Low Equivalent On-Resistance
- Complementary PNP Type: ZXTP25100CZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

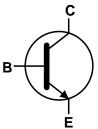
Case: SOT89

- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.05 grams (Approximate)

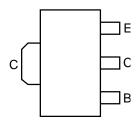
SOT89







Device Symbol



Top View Pin Out

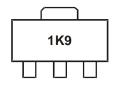
Ordering Information (Note 4)

| Part Number | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|---------------|------------|---------|--------------------|-----------------|-------------------|
| ZXTN25100DZTA | AEC-Q101 | 1K9 | 7 | 12 | 1,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1K9 = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | 180 | V |
| Collector-Emitter Voltage (Forward Blocking) | V _{CEX} | 180 | V |
| Collector-Emitter Voltage | V _{CEO} | 100 | V |
| Emitter-Collector Voltage (Reverse Blocking) | V _{ECO} | 6 | V |
| Emitter-Base Voltage | V _{EBO} | 7 | V |
| Continuous Collector Current | Ic | 2.5 | Α |
| Peak Pulse Current | I _{CM} | 3.5 | Α |
| Base Current | lΒ | 1 | Α |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|------------------|------------------|--------------|------------|--|
| | (Note 5) | | 1.1 8.8 | | |
| Power Dissipation | (Note 6) | | 1.8 14.4 | W mW/°C | |
| Linear Derating Factor | (Note 7) | P _D | 2.4 19.2 | | |
| | (Note 8) | | 4.46 35.7 | | |
| | (Note 5) | | 117 | | |
| Thermal Decistores, Junction to Ambient Air | (Note 6) | Б | 68 | °C/W | |
| Thermal Resistance, Junction to Ambient Air | (Note 7) | $R_{	heta JA}$ | 51 | | |
| | (Note 8) | | 28 | | |
| Thermal Resistance, Junction to Lead | (Note 9) | R _{0JL} | 7.95 | | |
| Operating and Storage Temperature Range | T_{J}, T_{STG} | -55 to +150 | °C | | |

ESD Ratings (Note 10)

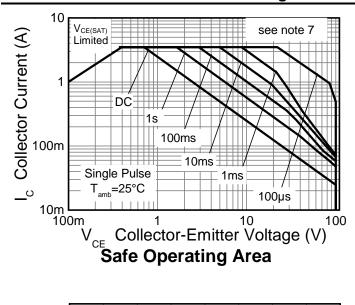
| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

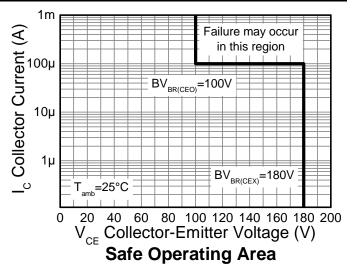
Notes:

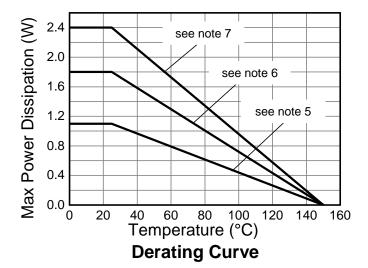
- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 0.6mm FR-4 PCB; device is measured For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copunder still air conditions whilst operating in a steady-state.
 Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 Same as Note 7, except the device is measured at t<5 seconds.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

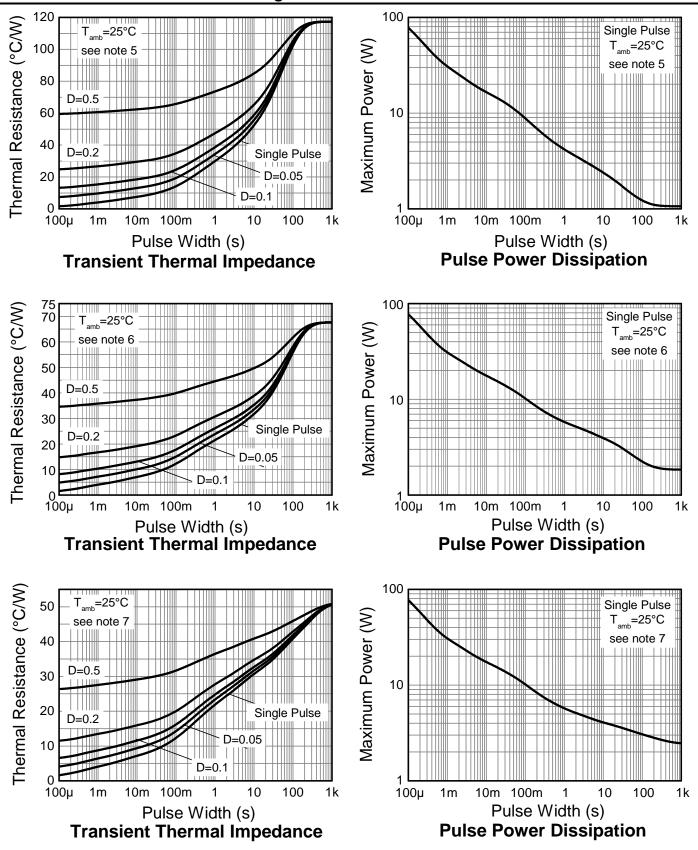








Thermal Characteristics and Derating Information





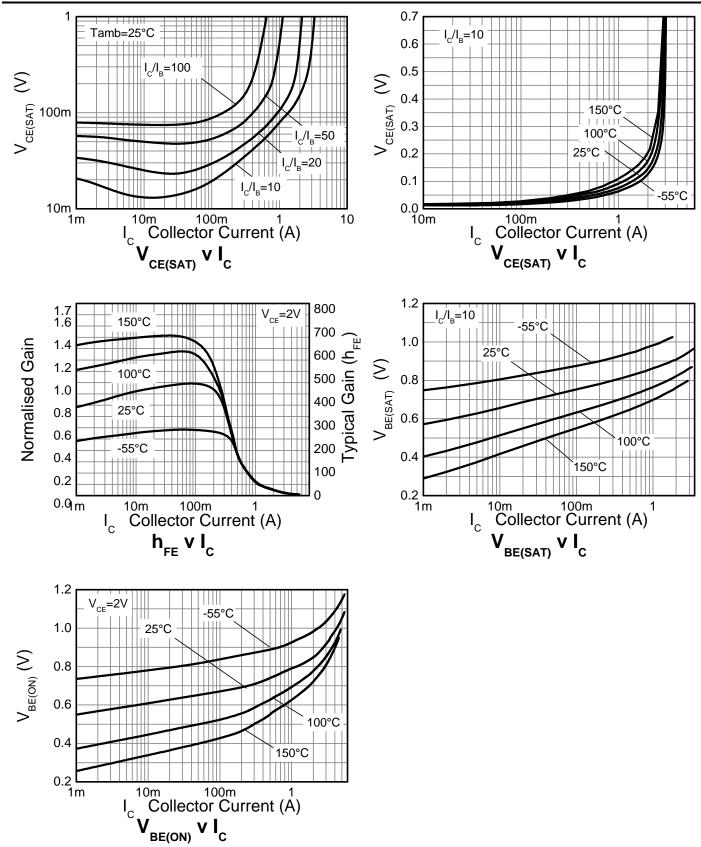
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|----------------------|-----------------------|------------------------|--------------------|----------|--|
| Collector-Base Breakdown Voltage | BV _{CBO} | 180 | 220 | _ | V | $I_C = 100\mu A$ |
| Collector-Emitter Breakdown Voltage (Forward Blocking) | BV _{CEX} | 180 | 220 | _ | V | $I_C = 100\mu A, R_{BE} < 1k\Omega \text{ or} -1V > V_{BE} > 0.25V$ |
| Collector-Emitter Breakdown Voltage (Note 11) | BV _{CEO} | 100 | 130 | _ | V | $I_C = 10mA$ |
| Emitter-Collector Breakdown Voltage (Reverse Blocking) | BV _{ECX} | 6 | 8.2 | _ | V | $I_E = 100\mu A$, $R_{BC} < 1k\Omega$ or $0.25V > V_{BC} > -0.25V$ |
| Emitter-Collector Breakdown Voltage (Reverse Blocking) | BV _{ECO} | 6 | 8.7 | _ | V | I _E = 100μA |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 7 | 8.3 | _ | V | $I_E = 100\mu A$ |
| Collector-Base Cutoff Current | I _{CBO} | _ | <1 | 50 0.5 | nA μA | V _{CB} = 180V V _{CB} = 180V, T _A = +100°C |
| Collector-Emitter Cutoff Current | I _{CEX} | _ | _ | 100 | nA | $V_{CE} = 100V, R_{BE} < 1k\Omega \text{ or}$ $1V < V_{BE} < 0.25V$ |
| Emitter Cutoff Current | I _{EBO} | _ | <1 | 50 | nA | V _{EB} = 5.6V |
| DC Current Transfer Static Ratio (Note 11) | h _{FE} | 300 120 40 — | 450 170 60 20 | 900 — — — | _ | $I_{C} = 10$ mA, $V_{CE} = 2$ V $I_{C} = 0.5$ A, $V_{CE} = 2$ V $I_{C} = 1$ A, $V_{CE} = 2$ V $I_{C} = 2.5$ A, $V_{CE} = 2$ V |
| Collector-Emitter Saturation Voltage (Note 11) | V _{CE(SAT)} | _ | 120 80 220 | 170 100 345 | mV | $I_C = 0.5A$, $I_B = 10mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 2.5A$, $I_B = 250mA$ |
| Base-Emitter Saturation Voltage (Note 11) | $V_{BE(SAT)}$ | _ | 935 | 1000 | mV | $I_C = 2.5A$, $I_B = 250mA$ |
| Base-Emitter Turn-on Voltage (Note 11) | V _{BE(ON)} | _ | 890 | 950 | mV | $I_C = 2.5A$, $V_{CE} = 2V$ |
| Transitional Frequency | f _T | _ | 175 | _ | MHz | $I_E = 50$ mA, $V_{CE} = 10$ V f = 100MHz |
| Input Capacitance | C _{IBO} | | 154 | 250 | pF | V _{EB} = 0.5V, f = 1MHz |
| Output Capacitance | Сово | _ | 8.7 | 15 | pF | V _{CB} = 10V, f = 1MHz |
| Delay Time | t _D | _ | 16.4 | _ | ns | |
| Rise Time | t _R | _ | 115 | _ | ns | $I_C = 500$ mA, $V_{CC} = 10$ V, |
| Storage Time | ts | | 763 | _ | ns | $I_{B1} = -I_{B2} = 50 \text{mA}$ |
| Fall Time | t _F | _ | 158 | _ | ns | |

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

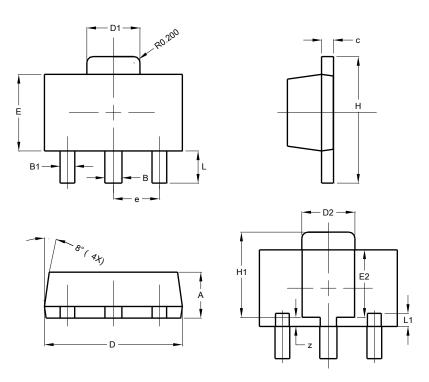




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

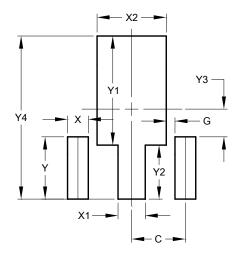


| SOT89 | | | | | |
|----------------------|-------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.40 | 1.60 | 1.50 | | |
| В | 0.50 | 0.62 | 0.56 | | |
| B1 | 0.42 | 0.54 | 0.48 | | |
| С | 0.35 | 0.43 | 0.38 | | |
| D | 4.40 | 4.60 | 4.50 | | |
| D1 | 1.62 | 1.83 | 1.733 | | |
| D2 | 1.61 | 1.81 | 1.71 | | |
| Е | 2.40 | 2.60 | 2.50 | | |
| E2 | 2.05 | 2.35 | 2.20 | | |
| е | - | - | 1.50 | | |
| Н | 3.95 | 4.25 | 4.10 | | |
| H1 | 2.63 | 2.93 | 2.78 | | |
| L | 0.90 | 1.20 | 1.05 | | |
| L1 | 0.327 | 0.527 | 0.427 | | |
| Z | 0.20 | 0.40 | 0.30 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



| Dimensions | Value (in mm) | | |
|------------|------------------|--|--|
| С | 1.500 | | |
| G | 0.244 | | |
| Х | 0.580 | | |
| X1 | 0.760 | | |
| X2 | 1.933 | | |
| Υ | 1.730 | | |
| Y1 | 3.030 | | |
| Y2 | 1.500 | | |
| Y3 | 0.770 | | |
| Y4 | 4.530 | | |

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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